



IN THE CLAIMS

Please amend the claim 1 to read as follows:

B.1
1. (Amended) A bottom-gate thin-film transistor comprising a gate electrode, a gate insulating film, an active layer, and a protective insulating film deposited in that order on a substrate; and

Sub C.5
various layers formed over said protective film with at least one electrode extending therethrough that is operatively and electrically connected to said active layer, LDD region or source-drain region;

wherein,

the protective insulating film has a thickness of 100 nm or less, and the protective insulating film is formed on any one of the active layer, an LDD region, and a source-drain region, and

there is no etched mask structure within the thin-film transistor structure.